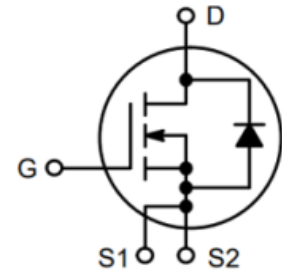


Features

- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Low switching loss
- Sense pin for optimized switching performance
- RoHS compliant with Halogen-free

HF

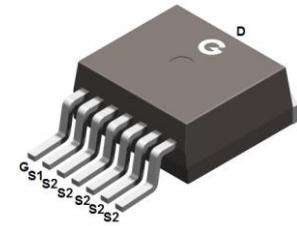


Applications

- Solar inverters
- Charger
- Uninterruptible Power Supply
- Switch Mode Power Supplies

Mechanical Data

- Case: TO-263-7
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



TO-263-7

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GSC120R080B7	TO-263-7	1000 pcs / Tape & Reel	GSC120R080B7

Maximum Ratings (@ $T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	1200	V
Gate-to-Source Voltage (transient)	V_{GS}	-10/+22	V
Gate-to-Source Voltage (static)		-5/+18	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	28	A
Continuous Drain Current ($T_c = 100^\circ\text{C}$)		20	A
Pulsed Drain Current	I_{DM}	79	A
Single Pulse Avalanche Energy ^{*2}	E_{AS}	128	mJ
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	158	W
Operating Junction Temperature Range	T_J	-55 ~ +175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	-	0.95	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air	$R_{\theta JA}$	-	-	40	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 100μA	1200	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1200V, V _{GS} = 0V	-	-	10	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = 22V, V _{DS} = 0V	-	-	100	nA
		V _{GS} = -10V, V _{DS} = 0V	-	-	-100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *1	V _{GS} = 18V, I _D = 12A, T _J = 25°C	-	80	100	mΩ
		V _{GS} = 18V, I _D = 12A, T _J = 175°C	-	120	-	
		V _{GS} = 15V, I _D = 12A, T _J = 25°C	-	100	130	
		V _{GS} = 15V, I _D = 12A, T _J = 175°C	-	130	-	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 5mA	2.1	-	3.5	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	2	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 800V f = 1MHz	-	1020	-	pF
C _{OSS}	Output Capacitance		-	70	-	
C _{RSS}	Reverse Transfer Capacitance		-	5	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *3	V _{DD} = 800V V _{GS} = -5/18V I _D = 12A R _G = 5Ω	-	7	-	ns
t _r	Turn-on Rise Time *3		-	8	-	
t _{d(OFF)}	Turn-Off Delay Time *3		-	17	-	
t _f	Turn-Off Fall Time *3		-	11	-	
E _{on}	Turn-On Energy *3		-	143	-	μJ
E _{off}	Turn-Off Energy *3		-	37	-	
Q _G	Total Gate-Charge	V _{DD} = 800V	-	50	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = -5/18V	-	17	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 12A	-	13	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *1	I _{SD} = 12A, V _{GS} = -5V, T _J = 25°C	-	4.0	-	V
		I _{SD} = 12A, V _{GS} = -5V, T _J = 175°C	-	3.6	-	
t _{rr}	Reverse Recovery Time	I _F = 12A, V _R = 800V	-	11	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 1000A/μs	-	65	-	nC

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 120V, V_{GS} = 18V, L = 1mH$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

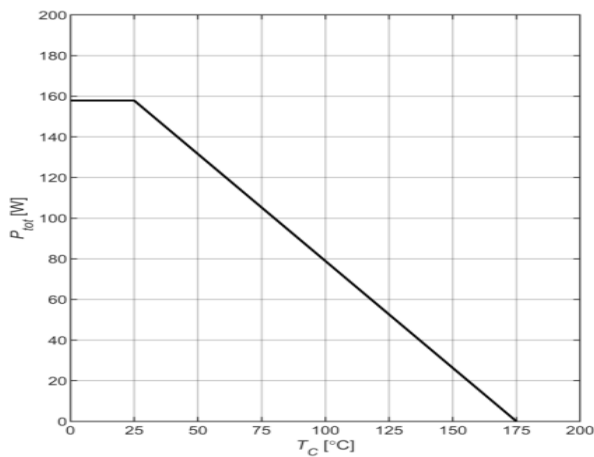


Fig 1 Power Dissipation

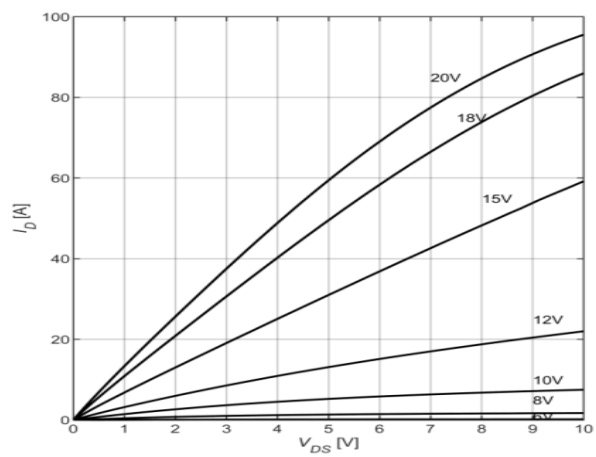


Fig 2 Typical Output Characteristics ($T_J = -55^\circ\text{C}$)

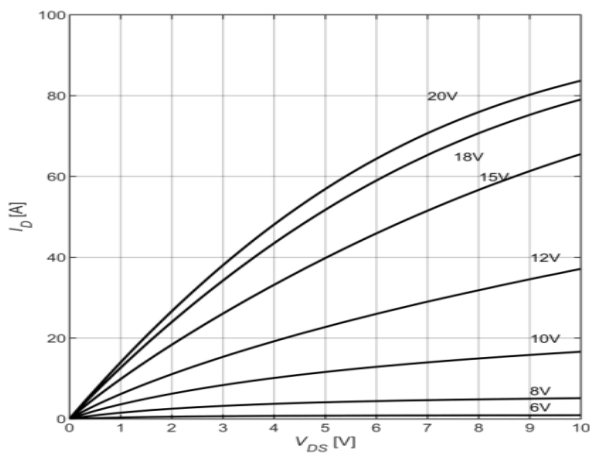


Fig 3 Typical Output Characteristics ($T_J = 25^\circ\text{C}$)

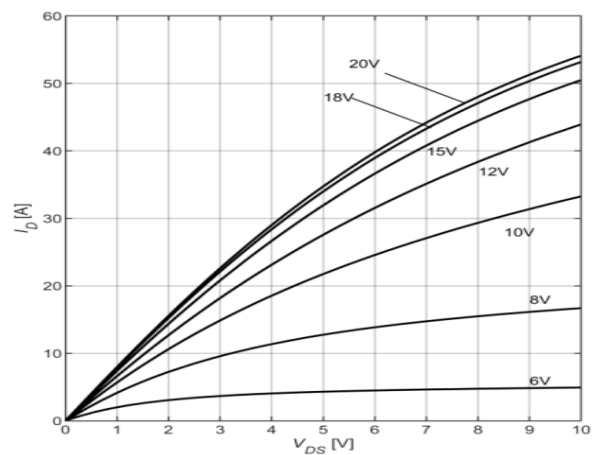


Fig 4 Typical Output Characteristics ($T_J = 175^\circ\text{C}$)

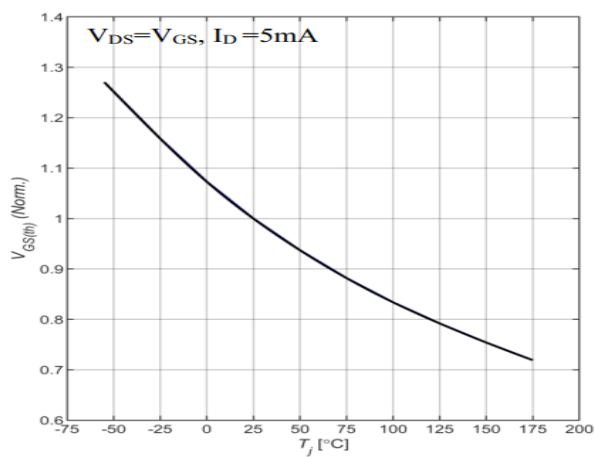


Fig 5 Normalized $V_{GS(th)}$ vs. Junction Temperature

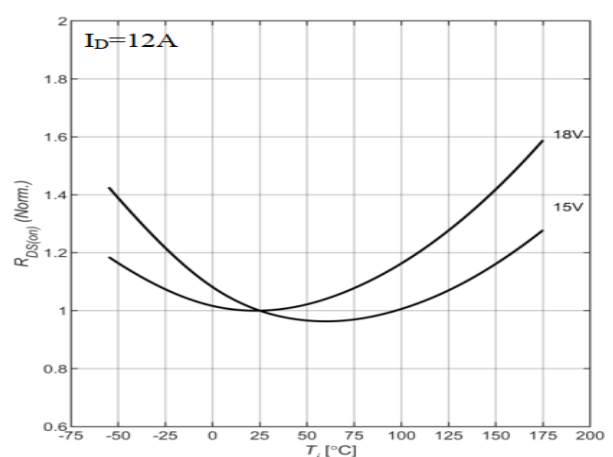


Fig 6 Normalized On-Resistance vs. Junction Temperature

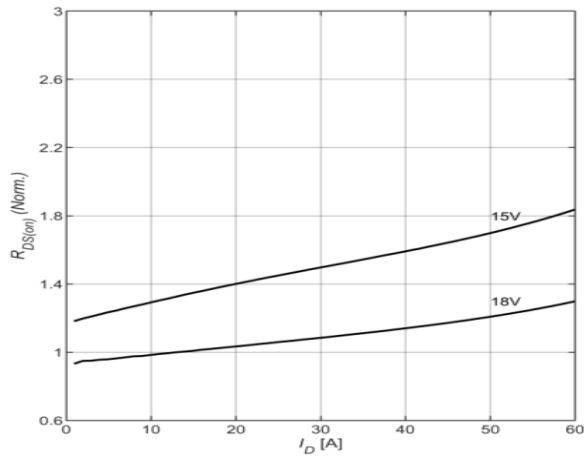


Fig 7 Normalized On-Resistance vs. Drain Current

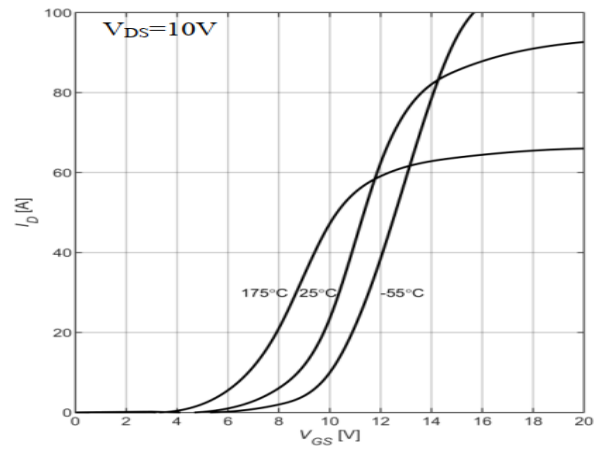


Fig 8 Transfer Characteristics

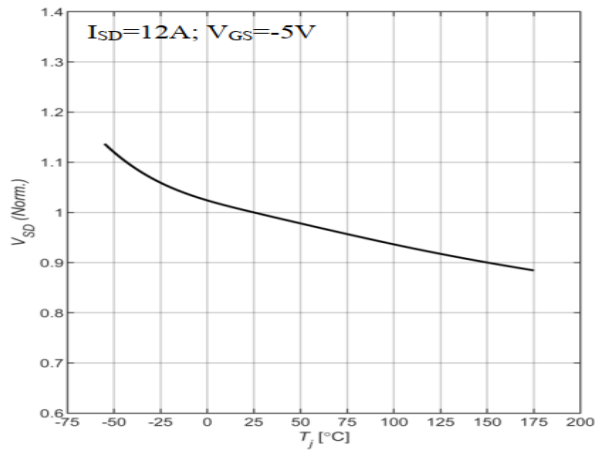


Fig 9 Normalized Diode Forward Voltage vs. Junction Temperature

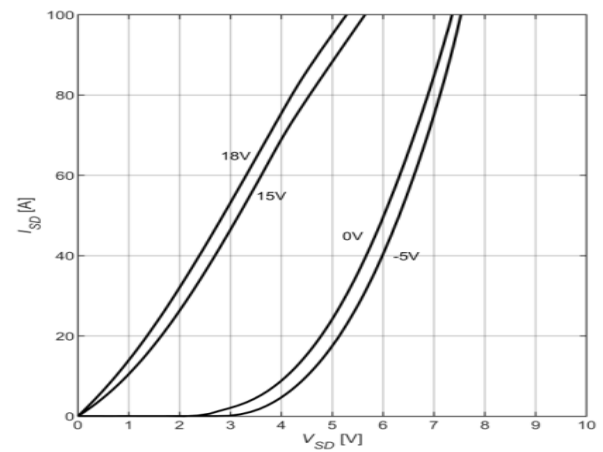


Fig 10 Body-Diode Characteristics ($T_J = -55^{\circ}\text{C}$)

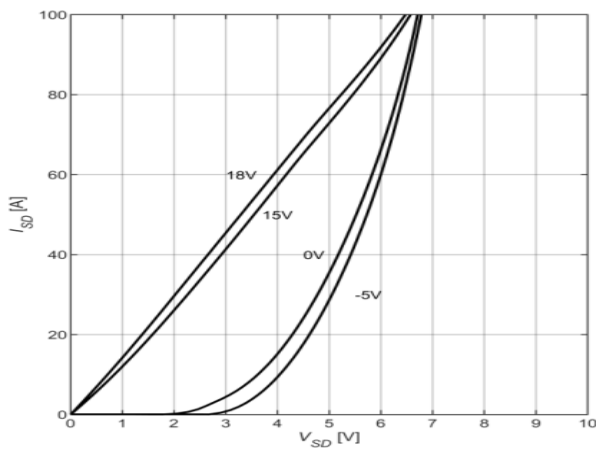


Fig 11 Body-Diode Characteristics ($T_J = 25^{\circ}\text{C}$)

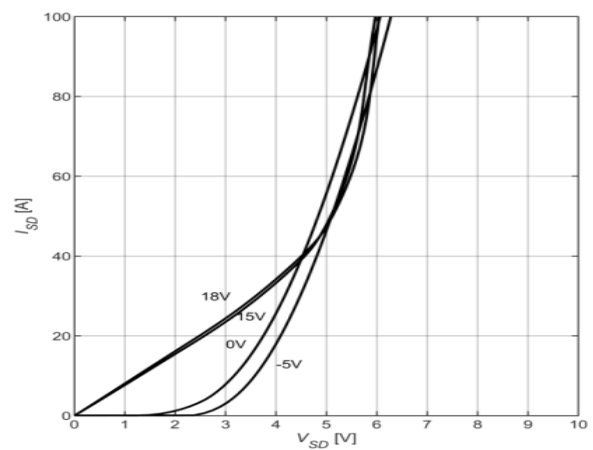


Fig 12 Body-Diode Characteristics ($T_J = 175^{\circ}\text{C}$)

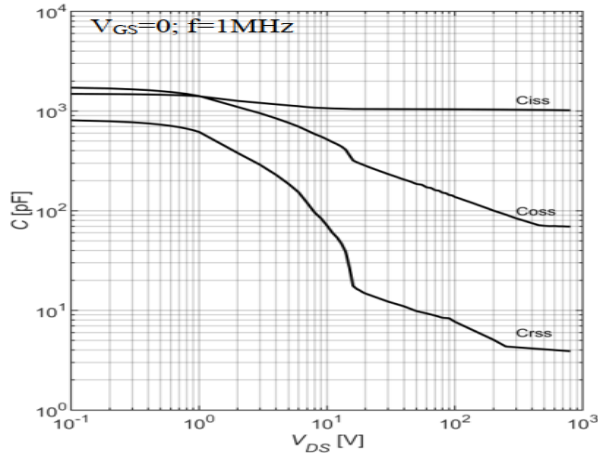


Fig 13 Capacitance Characteristics

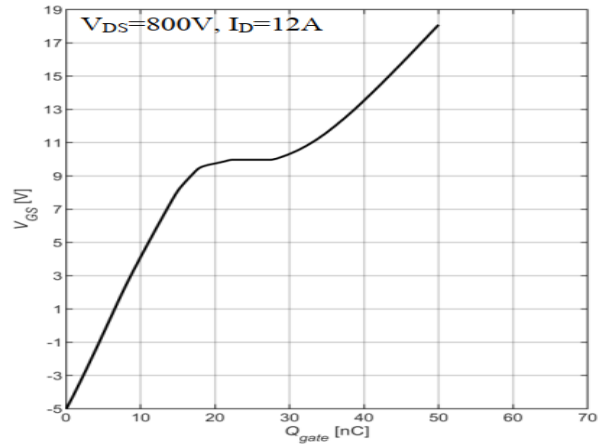


Fig 14 Gate-Charge Characteristics

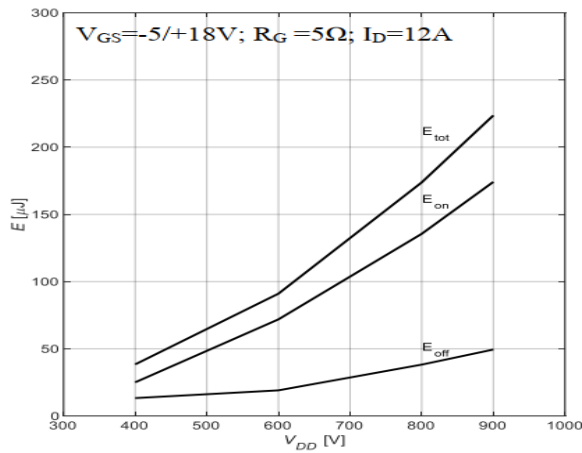


Fig 15 Output Capacitor Stored Energy

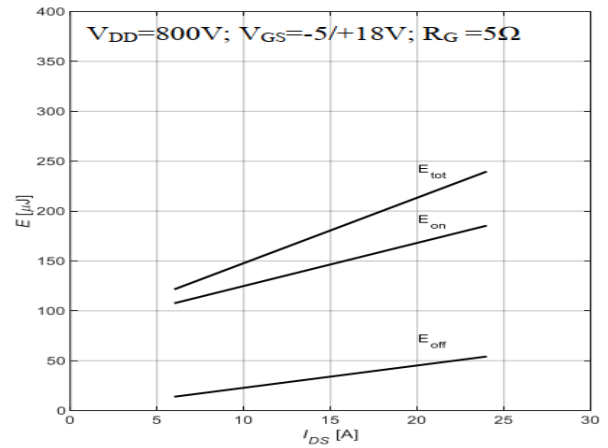


Fig 16 Clamped Inductive Switching Energy vs.
Drain Current

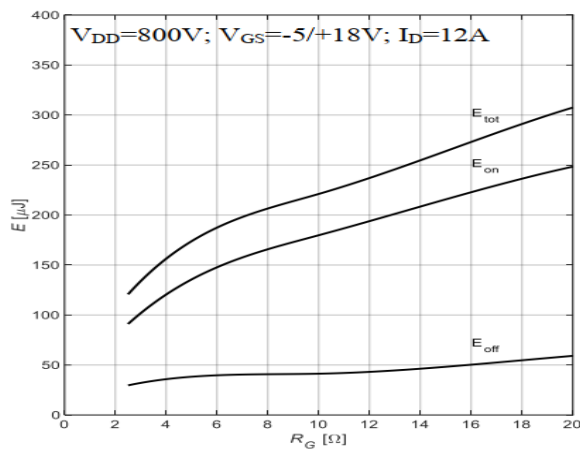


Fig 17 Clamped Inductive Switching Energy vs. R_G

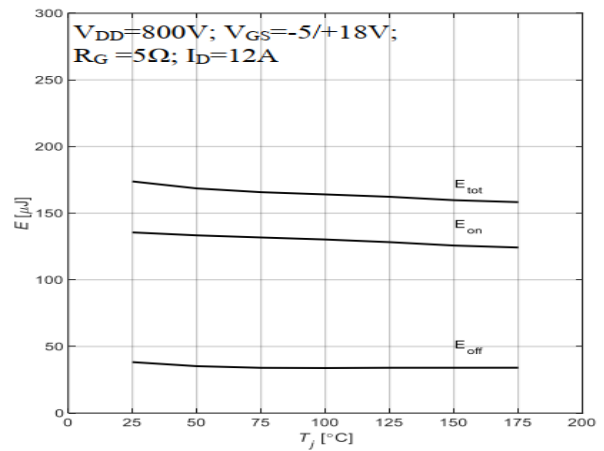


Fig 18 Clamped Inductive Switching Energy vs.
Junction Temperature

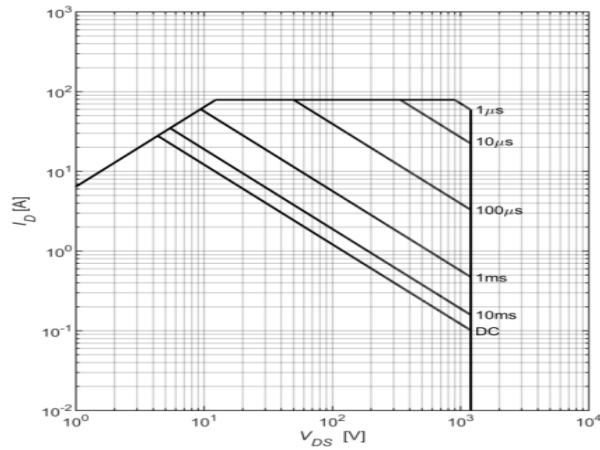


Fig 19 Safe Operating Area

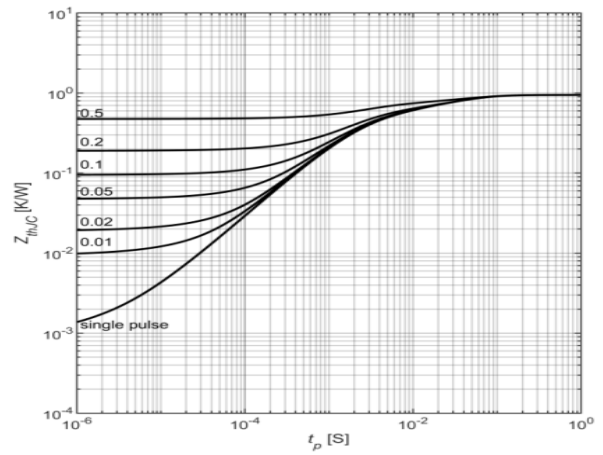
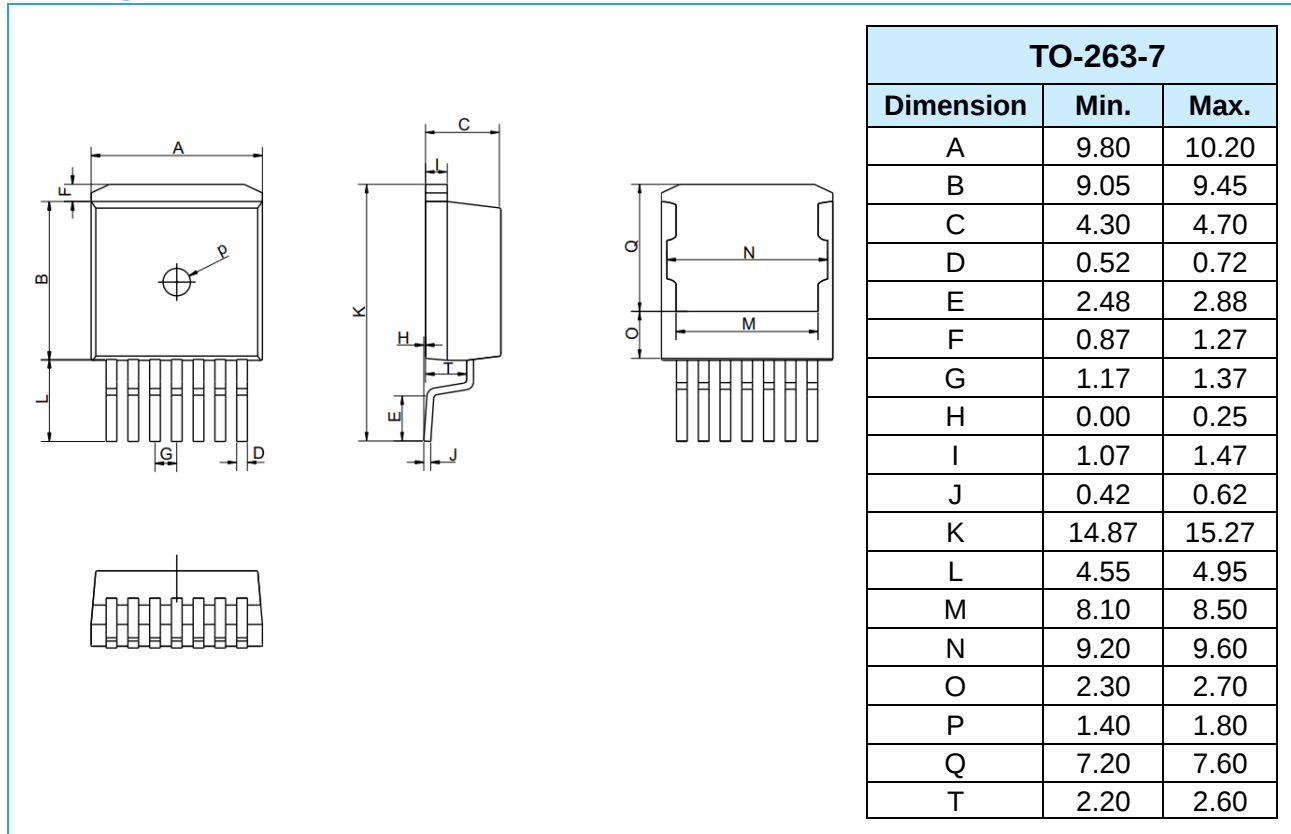


Fig 20 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

